

TPS22997 調整可能な立ち上がり時間、5.5V、10A、オン抵抗 4mΩ のロード・スイッチ

1 特長

- 動作入力電圧範囲 (V_{IN}): 0.1V~5.5V
- BIAS 電圧範囲: 1.5V~5.5V
- 最大連続電流: 10A
- オン抵抗 (R_{ON}): 4mΩ (標準値)
- 調整可能なスルー・レート制御
- 可変クイック出力放電 (QOD)
- オープン・ドレインのパワー・グッド (PG) 信号
- サーマル・シャットダウン
- 低い消費電力:
 - オン状態 (I_Q): 10μA (標準値)
 - オフ状態 (I_{SD}): 0.1μA (標準値)
- サーマル・シャットダウン
- ON ピンのスマート・プルダウン ($R_{PD,ON}$)
 - $ON \geq V_{IH}$ (I_{ON}): 25nA (標準値)
 - $ON \leq V_{IL}$ ($R_{PD,ON}$): 500kΩ (標準値)

2 アプリケーション

- ソリッドステート・ドライブ (SSD)
- PC とノート PC
- 産業用 PC
- 光学モジュール

3 概要

TPS22997 は、シングル・チャンネルのロード・スイッチで、立ち上がり時間を設定して突入電流を最小化できます。このデバイスは、0.1V~5.5V の入力電圧範囲で動作できる N チャンネル MOSFET を内蔵し、10A の最大連続電流をサポートできます。

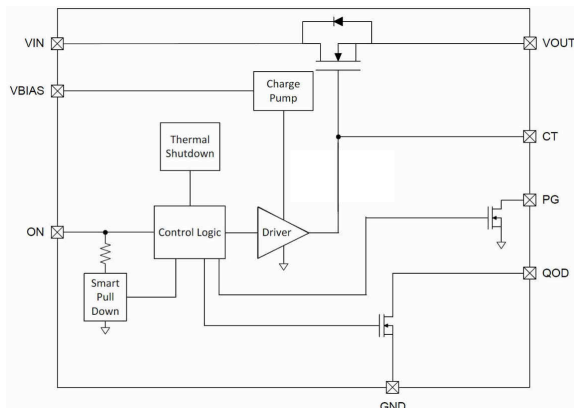
このスイッチは 1 本のイネーブル・ピン (ON) で制御されます。このイネーブル・ピンは低電圧の GPIO 信号 ($V_{IH} = 0.8V$) と直接接続できます。TPS22997 デバイスは、スイッチをオフにした際に出力を素早く放電させるためのオプションの QOD ピンを持っており、出力の立ち下がり時間 (t_{FALL}) は外付け抵抗で調整できます。本デバイスには、メイン MOSFET が完全にオンしていることを示すパワー・グッド (PG) 信号があります。この PG 信号を使って下流の負荷を有効にできます。サーマル・シャットダウン機能を内蔵しているため、高温環境でも確実に保護されます。

TPS22997 は、1.5 × 2.0mm、0.5mm ピッチの 10 ピン WQFN パッケージ (RYZ) で供給され、気温 -40°C ~ +125°C の範囲に渡って動作することが特徴です。

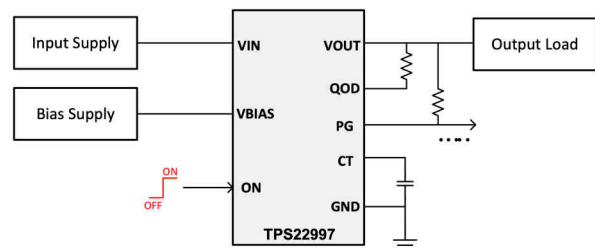
デバイス情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
TPS22997	WQFN (10)	1.5 × 2.0mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



TPS22997 のブロック図



TPS22997 の代表的なアプリケーション



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
December 2022	*	Initial Release

5 Pin Configuration and Functions

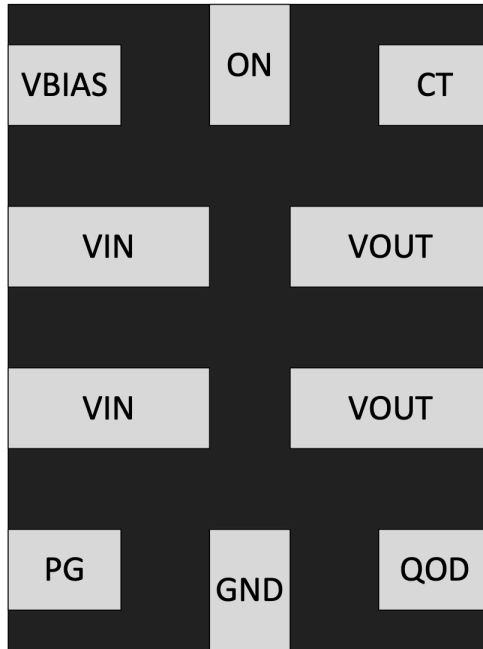


图 5-1. TPS22997 RYZ Package, 10-Pin WQFN (Top View)

表 5-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.		
VBIAS	1	I	Device bias supply
VIN	2, 3	I	Switch input
PG	4	O	Open drain power good signal, asserted high when the output is full load ready
GND	5	-	Device ground
QOD	6	-	Quick output discharge pin
VOUT	7, 8	O	Switch output
CT	9	I	Timing pin, can control the slew rate of the output through a capacitor to GND
ON	10	I	Enable pin

(1) I = Input, O = Output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{IN}	Input Voltage	-0.3	6	V
V _{BIAS}	Bias Voltage	-0.3	6	V
V _{ON} , V _{PG} , V _{QOD}	Control Pin Voltage	-0.3	6	V
V _{CT}	CT Pin Voltage		15	V
I _{MAX}	Maximum Current		10	A
T _J	Junction temperature		Internally Limited	°C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{IN}	Input Voltage	0.1		5.5	V
V _{BIAS}	Bias Voltage	1.5		5.5	V
V _{IH}	ON Pin High Voltage Range	0.8		5.5	V
V _{IL}	ON Pin Low Voltage Range	0		0.35	V
V _{PG} , V _{QOD}	Control Pin Voltage	0		5.5	V
T _A	Ambient Temperature	-40		125	°C

6.4 Thermal Information

THERMAL METRIC		TPS22997	UNIT
		RYZ (WQFN)	
		10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	83.7	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	73.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	18.2	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	2.0	°C/W
Υ _{JB}	Junction-to-board characterization parameter	18.1	°C/W

6.5 Electrical Characteristics (VBIAS = 5 V)

over operating free-air temperature range (unless otherwise noted). Typical values are specified at 25°C and VIN = 3.3V, VBIAS = 5.5V.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0V	25°C	0.1			µA
			-40°C to 85°C			0.5	µA
			-40°C to 125°C			1	µA
I _{Q,VBIAS}	VBIAS Quiescent Current	ON > V _{IH}	25°C	10			µA
			-40°C to 85°C			15	µA
			-40°C to 125°C			15	µA
I _{SD,VIN}	VIN Shutdown Current	ON = 0V	25°C	0.1			µA
			-40°C to 85°C			1	µA
			-40°C to 125°C			7	µA
I _{ON}	ON pin leakage	ON = VBIAS	-40°C to 125°C	0.1			µA
Performance							
R _{ON}	On-Resistance	VIN = 5V	25°C	4			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 3.3V	25°C	4			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 1.8V	25°C	4			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 1.2V	25°C	4			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 0.8V	25°C	4			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
V _{OL,PG}	Power Good VOL	I _{PG} = 1mA	-40°C to 125°C			0.2	V
R _{PD,ON}	Smart Pull Down Resistance		25°C	500			kΩ
			-40°C to 125°C			700	kΩ
R _{QOD}	QOD Resistance		25°C	50			Ω
			-40°C to 125°C			75	Ω
Protection							
TSD	Thermal Shutdown		-	150	170	190	°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

6.6 Electrical Characteristics (VBIAS = 3.3 V)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0V	25°C	0.1			µA
			-40°C to 85°C			0.5	µA
			-40°C to 125°C			1	µA

6.6 Electrical Characteristics (VBIAS = 3.3 V) (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
I _{Q,VBIAS}	VBIAS Quiescent Current	ON > V _{IH}	25°C		10		uA
			-40°C to 85°C			15	uA
			-40°C to 125°C			15	uA
I _{SD,VIN}	VIN Shutdown Current	ON = 0V	25°C		0.1		uA
			-40°C to 85°C			1	uA
			-40°C to 125°C			7	uA
I _{ON}	ON pin leakage	ON = VBIAS	-40°C to 125°C		0.1		uA
Performance							
R _{ON}	On-Resistance	VIN = 3.3V	25°C		4		mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 1.8V	25°C		4		mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 1.2V	25°C		4		mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 0.8V	25°C		4		mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
V _{OL,PG}	Power Good VOL	I _{PG} = 1mA	-40°C to 125°C			0.2	V
R _{PD,ON}	Smart Pull Down Resistance		25°C		500		kΩ
			-40°C to 125°C			700	kΩ
R _{QOD}	QOD Resistance		25°C		50		Ω
			-40°C to 125°C			100	Ω
Protection							
TSD	Thermal Shutdown		-	150	170	190	°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-		20		°C

6.7 Electrical Characteristics (VBIAS = 1.5 V)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0V	25°C		0.1		uA
			-40°C to 85°C			0.5	uA
			-40°C to 125°C			1	uA
I _{Q,VBIAS}	VBIAS Quiescent Current	ON > V _{IH}	25°C		10		uA
			-40°C to 85°C			15	uA
			-40°C to 125°C			15	uA
I _{SD,VIN}	VIN Shutdown Current	ON = 0V	25°C		0.1		uA
			-40°C to 85°C			1	uA
			-40°C to 125°C			7	uA
I _{ON}	ON pin leakage	ON = VBIAS	-40°C to 125°C		0.1		uA
Performance							

6.7 Electrical Characteristics (VBIAS = 1.5 V) (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
R _{ON}	On-Resistance	VIN = 1.5V	25°C	4.5			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 1.2V	25°C	4.5			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
R _{ON}	On-Resistance	VIN = 0.8V	25°C	4.5			mΩ
			-40°C to 85°C			6	mΩ
			-40°C to 125°C			7	mΩ
V _{OL,PG}	Power Good VOL	I _{PG} = 1mA	-40°C to 125°C			0.2	V
R _{PD,ON}	Smart Pull Down Resistance		25°C	500			kΩ
			-40°C to 125°C			700	kΩ
R _{QOD}	QOD Resistance		25°C	55			Ω
			-40°C to 125°C			100	Ω
Protection							
TSD	Thermal Shutdown		-	150	170	190	°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

6.8 Switching Characteristics (VBIAS = 5 V)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 5V						
t _{ON}	Turn ON time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		1170		us
t _{RISE}	Rise time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		819		us
t _D	Delay time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		347		us
t _{FALL}	Fall time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		2090		us
t _{OFF}	Turn OFF time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		108		us
VIN = 3.3V						
t _{ON}	Turn ON time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		944		us
t _{RISE}	Rise time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		567		us
t _D	Delay time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		377		us
t _{FALL}	Fall time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		2110		us
t _{OFF}	Turn OFF time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		113		us
VIN = 1.8V						
t _{ON}	Turn ON time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		692		us
t _{RISE}	Rise time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		327		us
t _D	Delay time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		365		us
t _{FALL}	Fall time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		2150		us
t _{OFF}	Turn OFF time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		117		us
VIN = 1.2V						
t _{ON}	Turn ON time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		591		us
t _{RISE}	Rise time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		227		us
t _D	Delay time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		364		us
t _{FALL}	Fall time	R _L = 100Ω, C _L = 10uF, CT = 1000pF		2180		us

6.8 Switching Characteristics (VBIAS = 5 V) (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		120		us
VIN = 0.8V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		523		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		159		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		365		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2260		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		129		us

6.9 Switching Characteristics (VBIAS = 3.3 V)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 3.3V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		898		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		563		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		336		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2100		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		108		us
VIN = 1.8V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		708		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		331		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		377		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2145		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		113		us
VIN = 1.2V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		605		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		231		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		375		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2190		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		119		us
VIN = 0.8V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		536		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		162		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		373		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2260		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		126		us

6.10 Switching Characteristics (VBIAS = 1.5 V)

over operating free-air temperature range (unless otherwise noted)

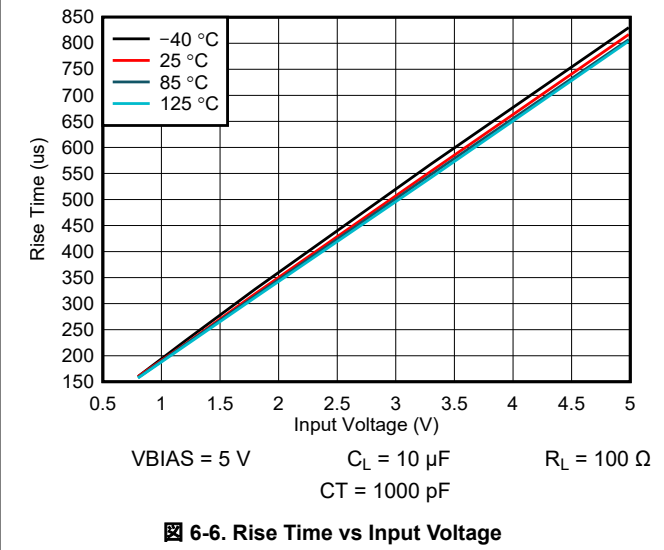
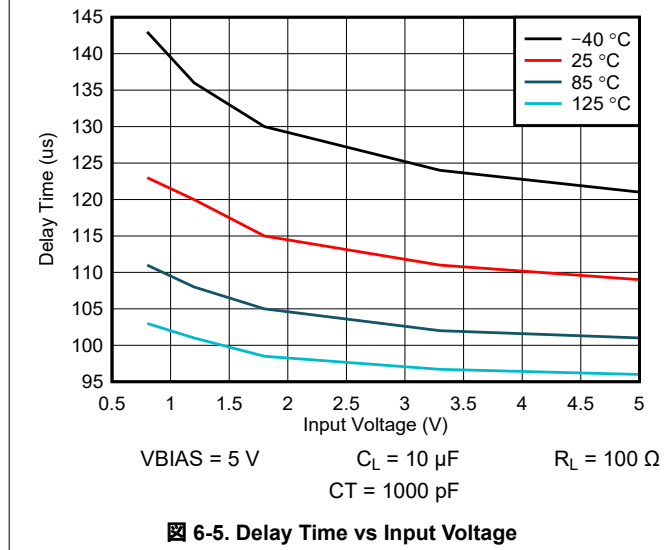
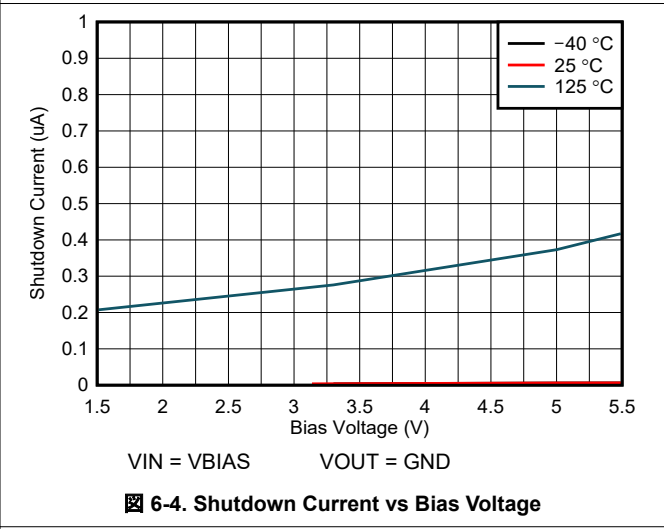
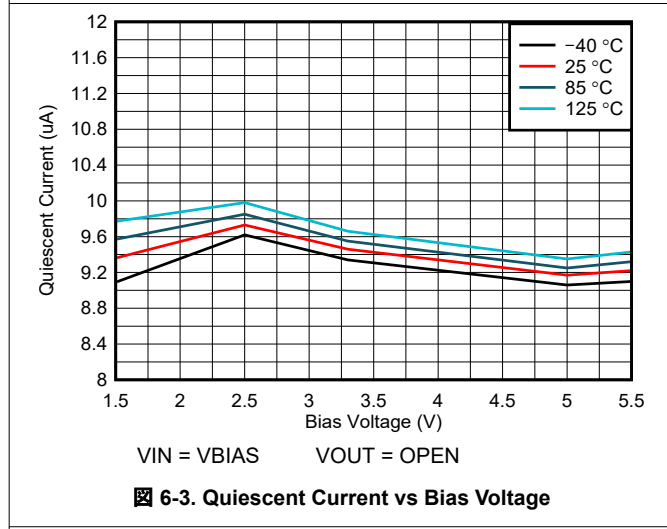
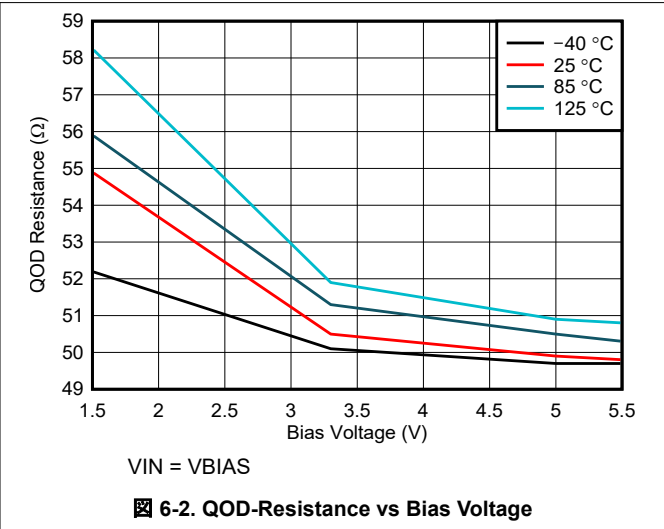
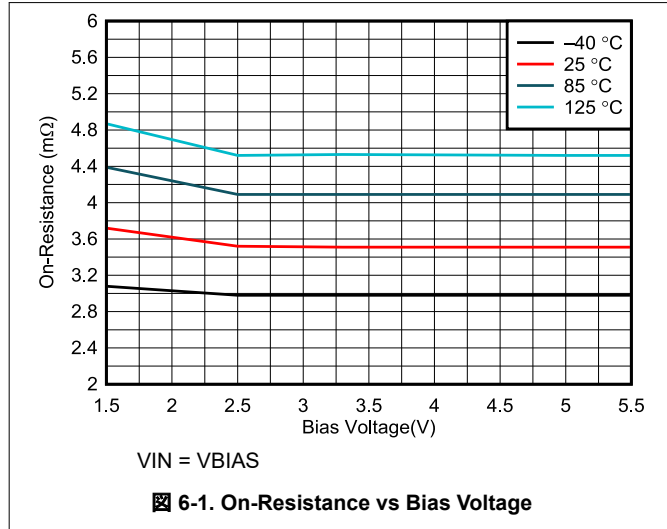
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 1.5V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		620		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		281		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		340		us

6.10 Switching Characteristics (VBIAS = 1.5 V) (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2150		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		111		us
VIN = 1.2V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		642		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		237		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		404		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2170		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		114		us
VIN = 0.8V						
tON	Turn ON time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		535		us
tRISE	Rise time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		166		us
tD	Delay time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		368		us
tFALL	Fall time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		2245		us
tOFF	Turn OFF time	$R_L = 100\Omega$, $C_L = 10\mu\text{F}$, $C_T = 1000\text{pF}$		171		us

6.11 Typical Characteristics



6.11 Typical Characteristics (continued)

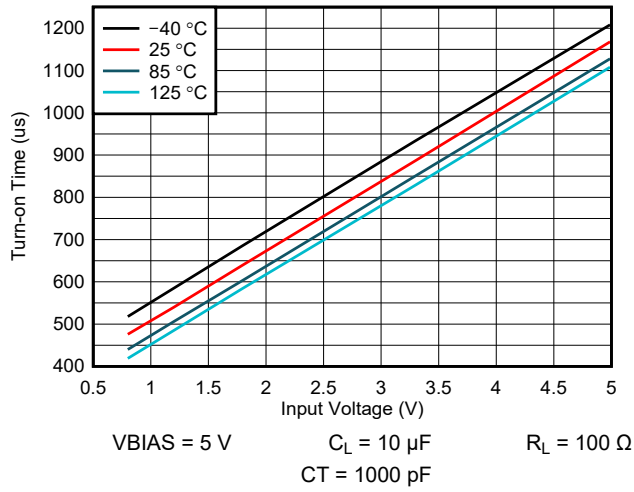


图 6-7. Turn-on Time vs Input Voltage

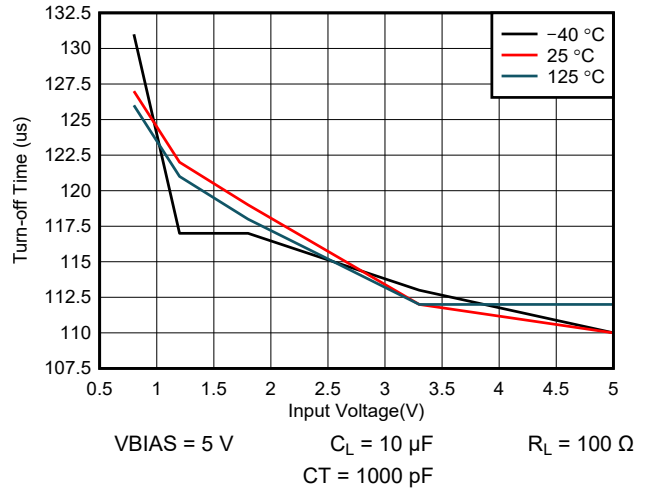


图 6-8. Turn-off Time vs Input Voltage

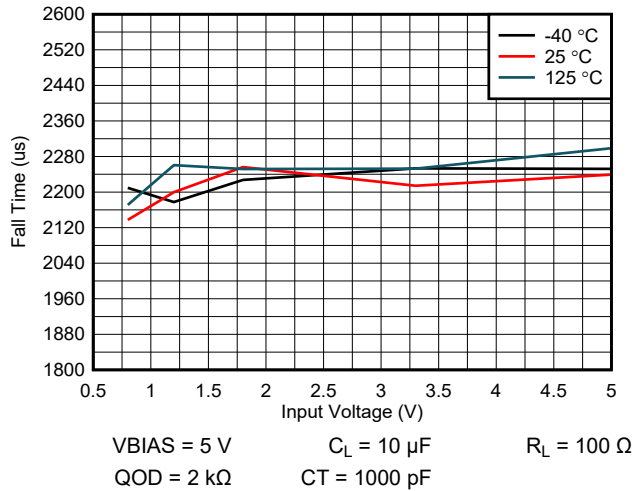


图 6-9. Fall Time vs Input Voltage

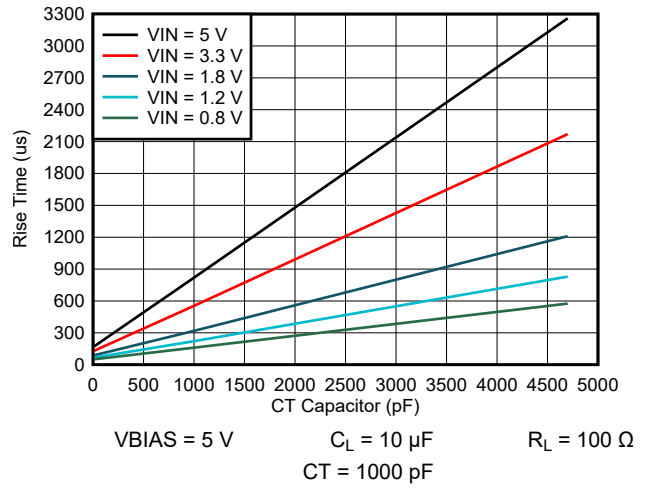
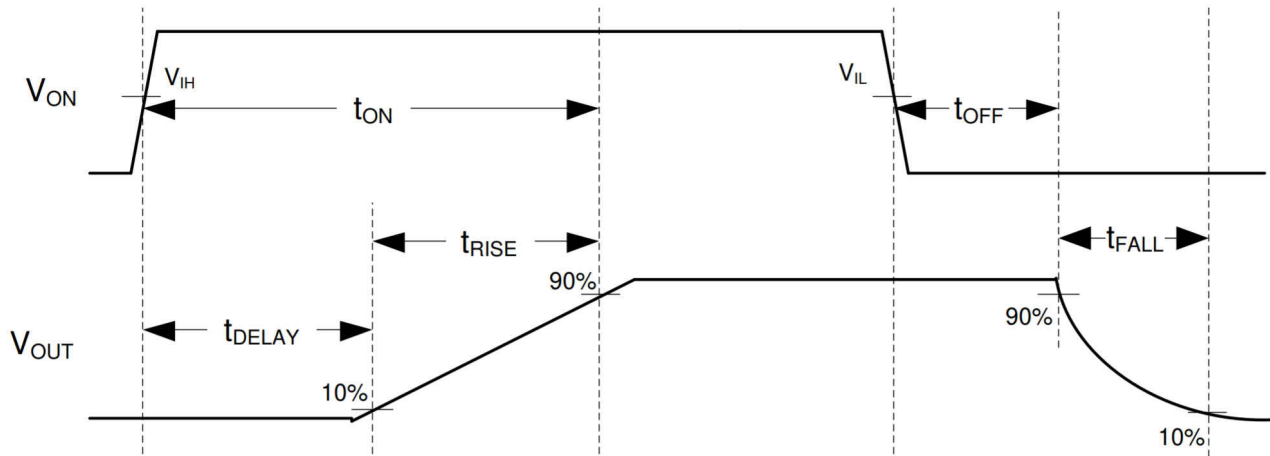


图 6-10. Rise Time vs CT Capacitor

7 Parameter Measurement Information



7-1. TPS22997 Timing Diagram

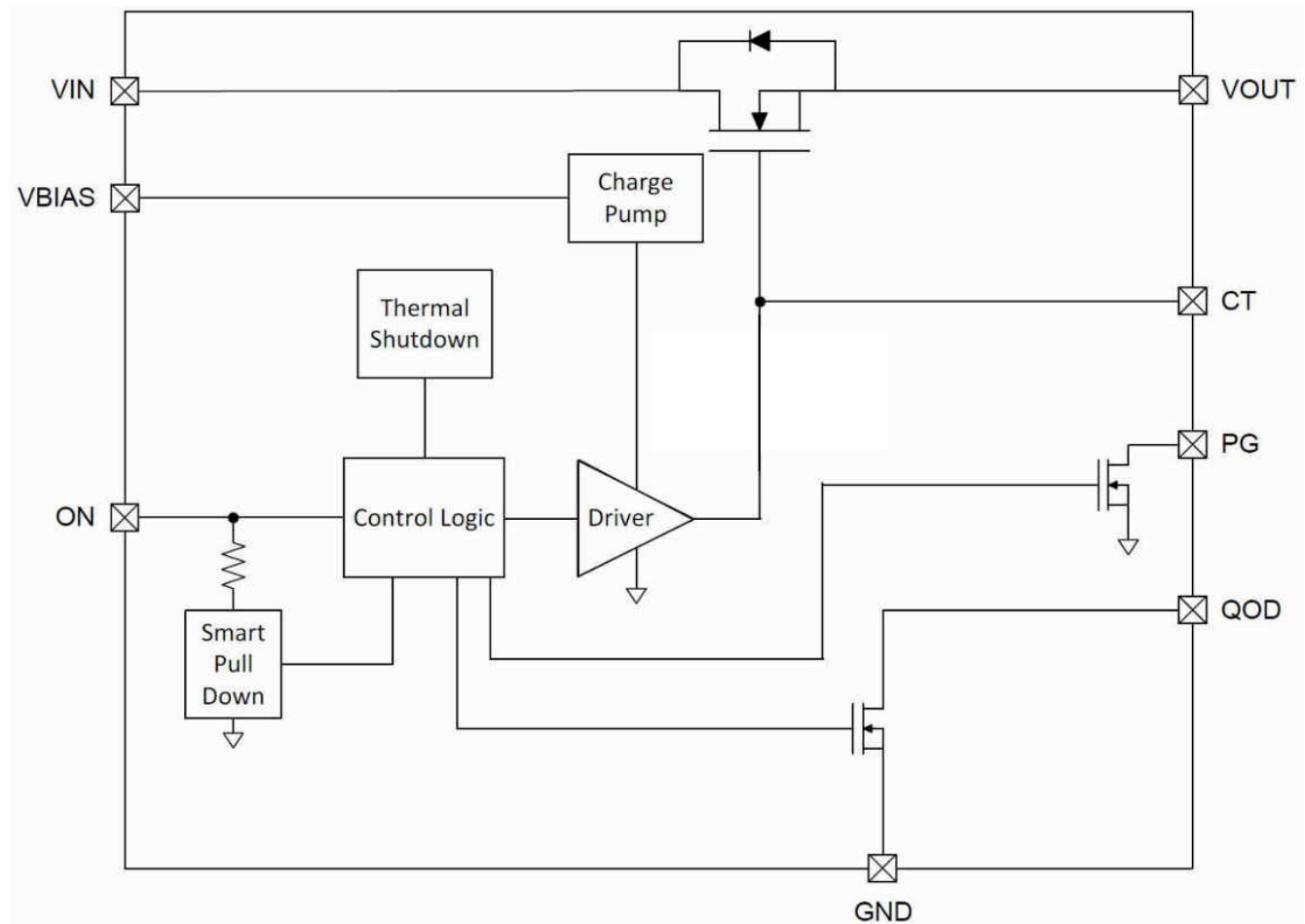
8 Detailed Description

8.1 Overview

The TPS22997 device is a single-channel load switch with a 4-mΩ power MOSFET designed to operate up to 10 A. The voltage range is 0.1 V to 5.5 V. A configurable rise time provides flexibility for power sequencing and minimizes inrush current for high capacitance loads.

The switch is controlled by an enable pin (ON), which is capable of interfacing directly with low voltage GPIO signals down to its V_{IH} level of 0.8 V. The TPS22997 device has an optional QOD pin for quick output discharge when switch is turned off, and the fall time (t_{FALL}) of the output can be adjusted through an external capacitor. There is a Power Good (PG) signal on the device that indicates when the main MOSFET is fully turned on and the on-resistance is at its final value.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 ON and OFF Control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold so it can be used in a wide variety of applications. When the pin pull high, the device enables, and when it is low, the device disables.

8.3.2 Adjustable Slew Rate

A capacitor to GND on the CT pin sets the slew rate, and the higher the capacitance the lower the slew rate. The voltage on the CT pin can be as high as 15 V; therefore, the minimum voltage rating for the CT capacitor must be 30 V for optimal performance. Rise times for VBIAS = 5 V are shown below.

CT Capacitor	VIN = 5 V	VIN = 3.3 V	VIN = 1.8 V	VIN = 1.2 V	VIN = 0.8 V
0 pF	165 μs	126 μs	86 μs	66 μs	51 μs
220 pF	309 μs	221 μs	137 μs	99 μs	74 μs
1000 pF	819 μs	554 μs	319 μs	222 μs	160 μs
4700 pF	3260 μs	2170 μs	1210 μs	829 μs	575 μs

The following equation can be used to estimate the rise time for different VIN and CT capacitors at VBIAS = 5 V.

$$t_R = (0.1302 V_{IN} + 0.0063) \times CT + 27.797 V_{IN} + 30.54 \quad (1)$$

Where:

- t_R = Rise time in μs
- V_{IN} = Input voltage in V
- CT = CT capacitance in pF

8.3.3 Adjustable Quick Output Discharge

The TPS22997 device includes a QOD feature that can be configured in one of three ways:

1. QOD pin shorted to VOUT pin. Using this method, the discharge rate after the switch becomes disabled is controlled with the value of the internal resistance RQOD. The value of this resistance is listed in the Electrical Characteristics table.
2. QOD pin connected to VOUT pin using an external resistor R_{EXT} . After the switch becomes disabled, the discharge rate is controlled by the value of the total resistance of the QOD.
3. QOD pin is unused and left floating. Using this method, there is no quick output discharge functionality, and the output remains floating after the switch is disabled.

Fall time is dependent on the strength of the configured pulldown resistance on the output.

8.3.4 Thermal Shutdown

When the device temperature reaches 150°C (typical), the device shuts itself off to prevent thermal damage. After it cools off by about 20°C, the device turns back on. If the device is kept in a thermally stressful environment, then the device oscillates between these two states until it can keep its temperature below the thermal shutdown point.

8.3.5 Power Good (PG) Signal

The TPS22997 device has a Power Good (PG) output signal to indicate the gate of the pass FET is driven high and the switch is on with the on-resistance close to its final value (full load ready). The signal is an active high and open drain output which can be connected to a voltage source through an external pullup resistor, R_{PU} . This voltage source can be VOUT from the TPS22997 device or another external voltage. VBIAS is required for PG to have a valid output.

8.4 Device Functional Modes

The below table summarizes the device functional modes:

ON	Fault Condition	VOUT State
L	N/A	Hi-Z
H	None	V_{IN} (through R_{ON})

ON	Fault Condition	VOUT State
X	Thermal shutdown	Hi-Z

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

This section highlights some of the design considerations when implementing this device in various applications.

9.2 Typical Application

This typical application demonstrates how to use the TPS22997 device to limit startup inrush current.

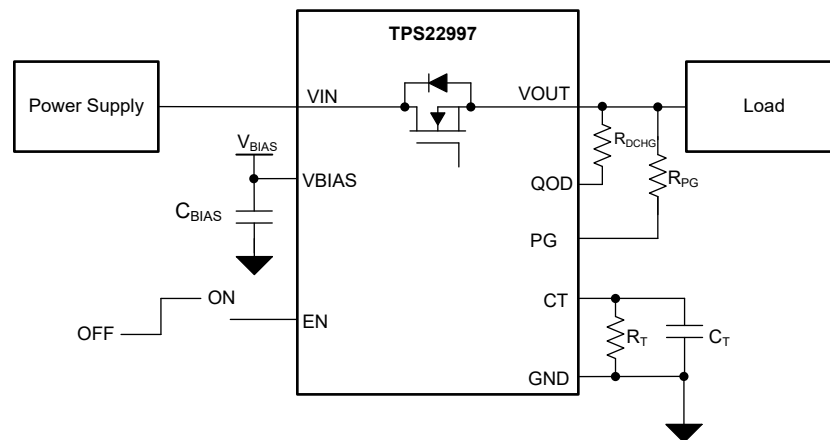


图 9-1. TPS22997 Basic Application

表 9-1. Component Descriptions

PARAMETER	Purpose
C_{BIAS}	Stabilize the bias supply and filter out low frequency noise.
C_T	Adjustable rise time capacitor.
R_T	Optional C_T capacitor discharge resistor for cases when device is disabled before output has fully ramped up. Use a resistor $>10M\Omega$.
R_{DCHG}	Adjustable output discharge resistor.

9.2.1 Design Requirements

For this example, the values below are used as the design parameters.

表 9-2. Design Parameters

PARAMETER	VALUE
V_{BIAS}	5.0 V
V_{IN}	5.0 V
Load capacitance	220 μ F
Maximum inrush current	1.5 A

9.2.2 Detailed Design Procedure

When the switch enables, the charge up the output capacitance from 0 V to the set value (1.8 V in this example). This charge arrives in the form of inrush current. Calculate inrush current using 式 2.

$$\text{Inrush Current} = C_L \times dV_{OUT}/dt \quad (2)$$

Where:

- C_L is the output capacitance.
- dV_{OUT} is the change in V_{OUT} during the ramp up of the output voltage when device is enabled. Because rise time is 10% of V_{OUT} to 90% of V_{OUT} , this is 80% of the V_{IN} value.
- dt is the rise time in V_{OUT} during the ramp up of the output voltage when the device is enabled.

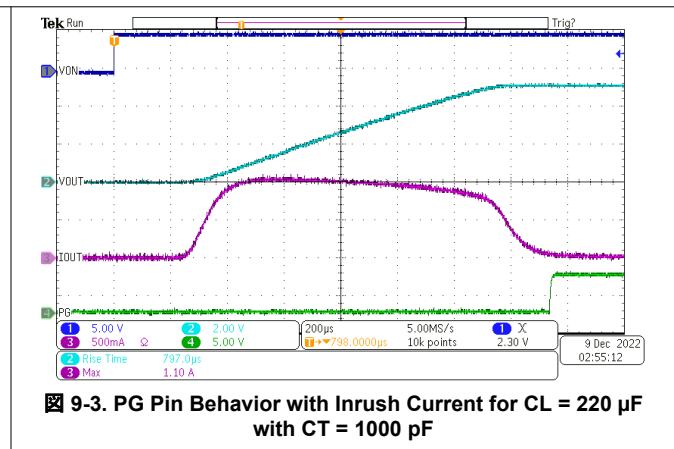
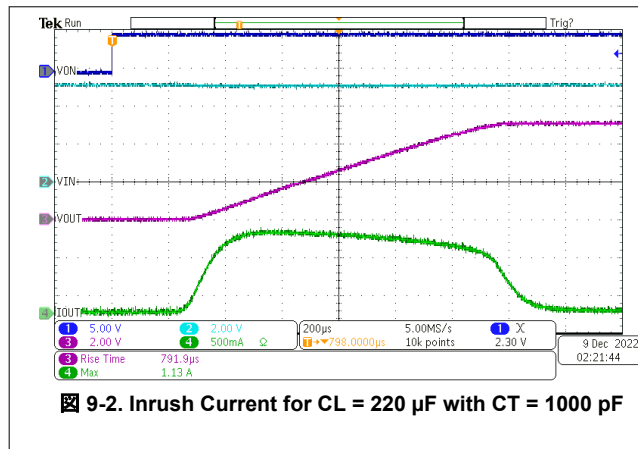
The TPS22997 offers an adjustable rise time for V_{OUT} , allowing the user to control the inrush current during turn on. Calculate the appropriate rise time using the design requirements and the inrush current equation as shown below.

$$1.5 \text{ A} = 220 \mu\text{F} \times (5.0 \text{ V} \times 80\%) / dt \quad (3)$$

$$dt = 586 \mu\text{s} \quad (4)$$

To ensure an inrush current of less than 1.5 A, a C_T setting that yields a rise time of more than 586 μs must be chosen. By using a 1000pF capacitance, a rise time of 819 μs is selected, limiting the inrush current to below 1.5 A.

9.2.3 Application Performance Plots



9.3 Power Supply Recommendations

The TPS22997 device is designed to operate with a V_{IN} range of 0.1 V to 5.5 V. Regulate the V_{IN} power supply well. The power supply must be able to withstand all transient load current steps. In most situations, using an input capacitance (C_{IN}) of 1 μF is sufficient to prevent the supply voltage from dipping when the switch is turned on. In cases where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance can be required on the input.

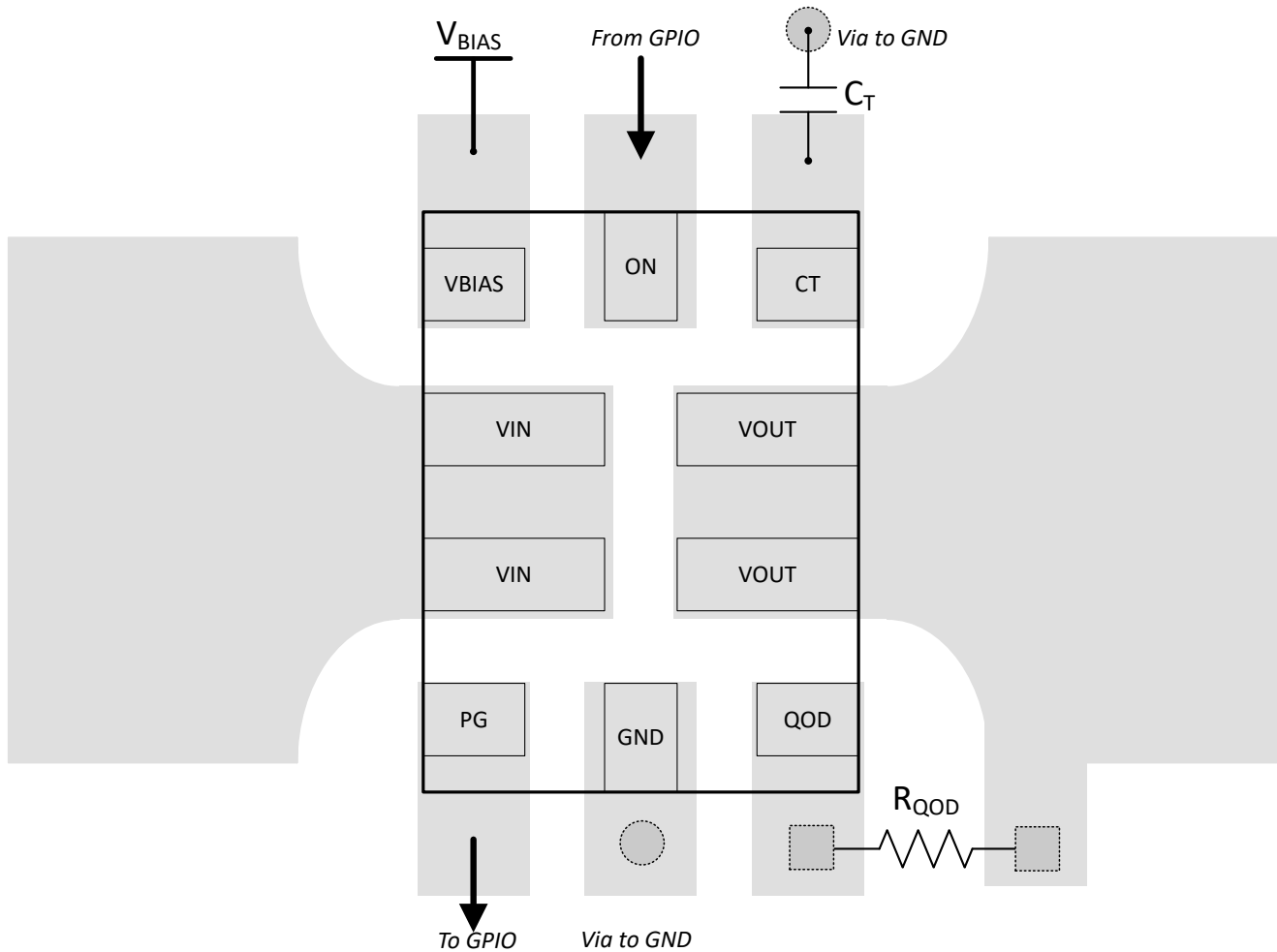
A capacitor (C_{BIAS}) is recommended to be placed as close to the device as possible to stabilize the supply and filter our low frequency noise.

9.4 Layout

9.4.1 Layout Guidelines

For best performance, all traces must be as short as possible. To be most effective, place the input and output capacitors close to the device to minimize the effects that parasitic trace inductances can have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects.

9.4.2 Layout Example



9-4. TPS22997 Layout Example

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 ドキュメントの更新通知を受け取る方法

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10.5 用語集

[テキサス・インスツルメンツ用語集](#)

この用語集には、用語や略語の一覧および定義が記載されています。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22997RYZR	ACTIVE	WQFN-HR	RYZ	10	3000	RoHS & Green	Call TI SN NIPDAU	Level-2-260C-1 YEAR	-40 to 125	(102, 1O2)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

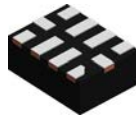
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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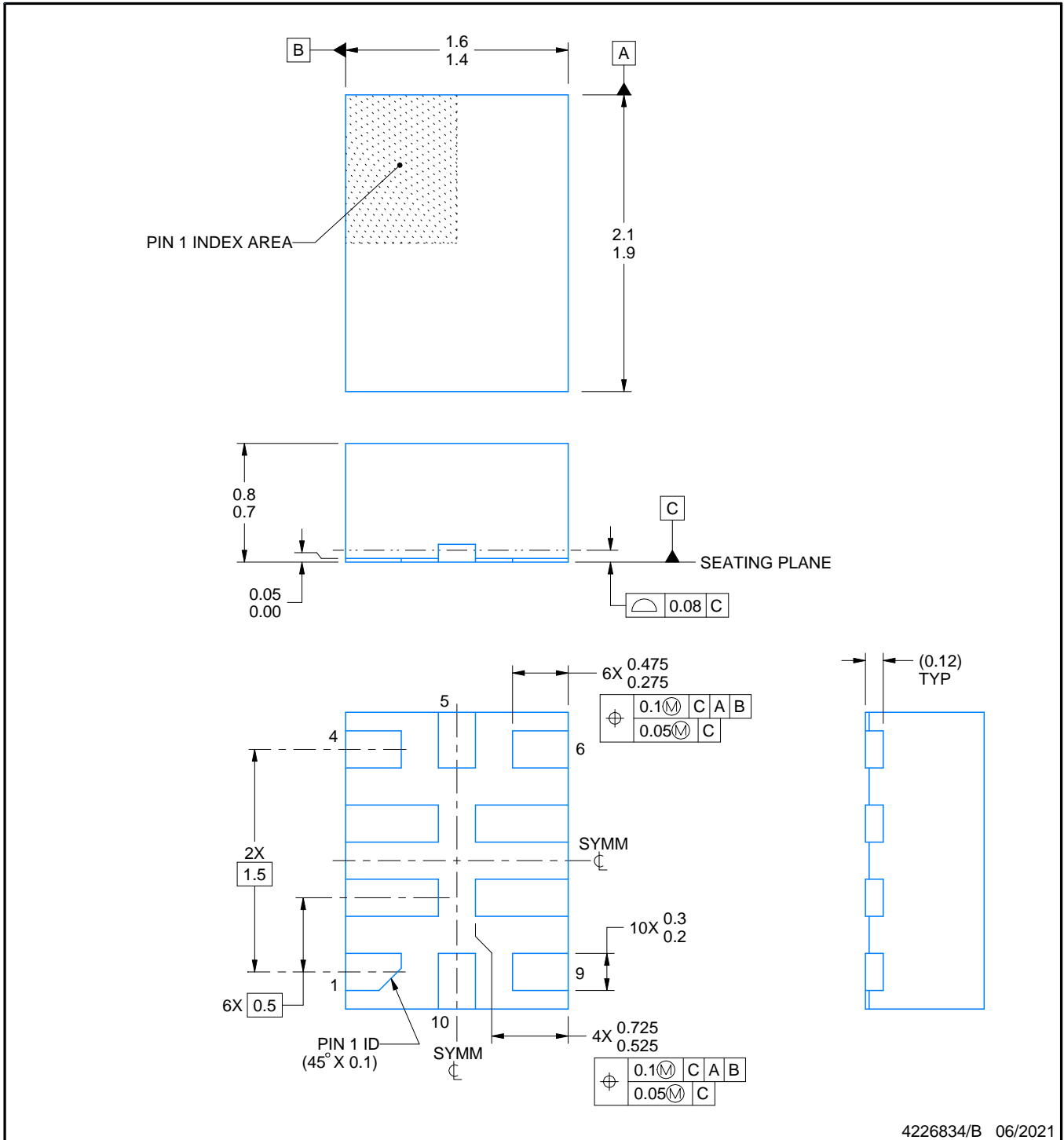
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RYZ0010A



PACKAGE OUTLINE
WQFN-HR - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4226834/B 06/2021

NOTES:

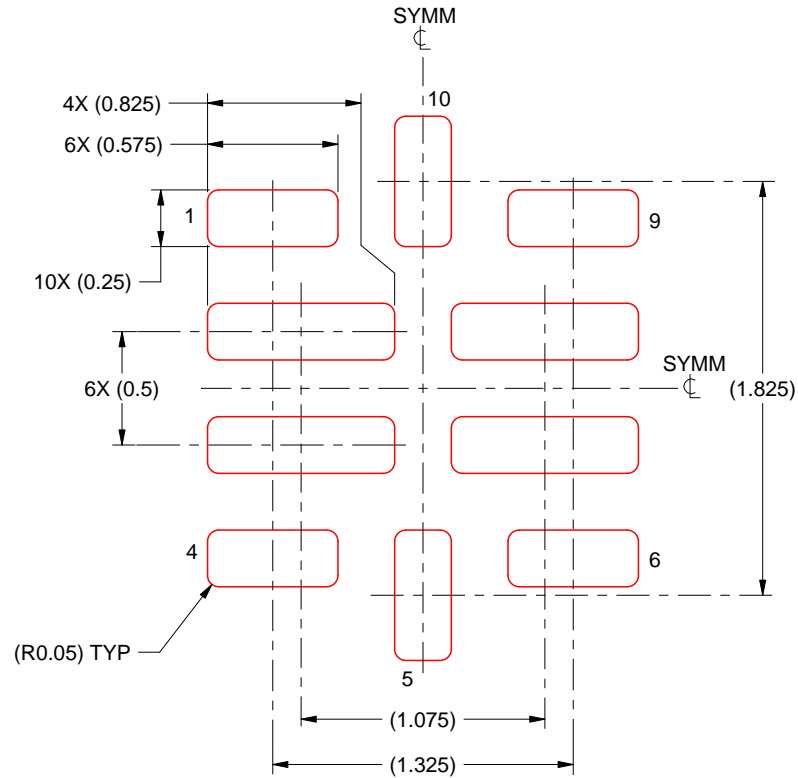
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE STENCIL DESIGN

RYZ0010A

WQFN-HR - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICKNESS
SCALE: 30X

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NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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